PTO/SB/21 (09-04)

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(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

Application Number	10/514,429
Filing Date	July 12, 2005
First Named Inventor	Robert DWILINSKI
Art Unit	2879
Examiner Name	Not Yet Assigned
Attorney Docket Number	204552033800

ENCLOSURES (Check all that apply)						
Fee Transi	mittal Form	Drawing(s)		After Allowance Communication to TC		
Fee	Attached	Licensing-related Papers		Appeal Communication to Board of Appeals and Interferences		
Amendme	nt/Reply	Petition		Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)		
After	Final	Petition to Convert to a Provisional Application		Proprietary Information		
Affid	avits/declaration(s)	Power of Attorney, Revocation Change of Correspondence Ac		Status Letter		
Extension	of Time Request	Terminal Disclaimer		X Other Enclosure(s) (please Identify below):		
Express Abandonment Request		Request for Refund		<ol> <li>Form PTO/SB/08a/b (1 page)</li> <li>Copies of IDS Citations (6 refs)</li> </ol>		
x Information	n Disclosure Statement	CD, Number of CD(s)		3. Return Receipt Postcard		
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Reply to Missing Parts/ Incomplete Application		Remarks				
Reply to Missing Parts under 37 CFR 1.52 or 1.53						
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT						
Firm Name						
MORRISON & FOERSTER LLP Signature						
1 Der N						
Printed name	Raj S. Davé	,				
Date	December 19, 2005	R	leg. No.	42,465		
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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Robert DWILINSKI et al.

Serial No.: 10/514,429

Filing Date: July 12, 2005

For: PHOSPHOR SINGLE CRYSTAL

SUBSTRATE AND METHOD FOR PREPARING THE SAME, AND

NITRIDE SEMICONDUCTOR DEVICE

USING THE SAME

Examiner: Not Yet Assigned

Group Art Unit: 2879

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97 & 1.98

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

## Dear Sir:

Pursuant to 37 C.F.R. § 1.97 and § 1.98, Applicants submit for consideration in the above-identified application the documents listed on the attached Form PTO/SB/08a/b. Copies of the non-patent literature are also submitted herewith. The Examiner is requested to make these documents of record.

Six of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 13-18) were cited in a Notification mailed September 27, 2005, directed to a related foreign application JP2003-503864, and have not been previously cited; one of the documents listed on the attached Form PTO/SB/08a/b (Cite No. 12) was cited in an Office Action mailed October 19, 2005, directed to a related application US 10/147,319, and has not been previously cited; two of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 1 and 2) were cited in an Office Action mailed October 4, 2005, directed to a related application US 10/479,858, and have not been previously cited; and nine of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 3-11) were cited in an Office Action mailed November 4, 2005, directed to a related

Atty. Docket No. 204552033800

'U.S. Serial No. 10/514,429

application US 10/493,747, and have not been previously cited. A certification under 37 C.F.R.

§ 1.97(e)(1) follows:

I hereby certify that each item of information was first cited in any communication

from a foreign patent office in a counterpart foreign application not more than three months prior

to the filing of this Supplemental Information Disclosure Statement.

This Information Disclosure Statement is submitted within three months of the

application filing date or before mailing of a first Office Action on the merits; accordingly, no

fee or separate requirements are required.

Applicants would appreciate the Examiner initialing and returning the Form

PTO/SB/08a/b, indicating that the information has been considered and made of record herein.

The information contained in this Supplemental Information Disclosure Statement

under 37 C.F.R. § 1.97 and § 1.98 is not to be construed as a representation that: (i) a complete

search has been made; (ii) additional information material to the examination of this application

does not exist; (iii) the information, protocols, results and the like reported by third parties are

accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

In the unlikely event that the transmittal form is separated from this document and the

Patent Office determines that an extension and/or other relief (such as payment of a fee under 37

C.F.R. § 1.17 (p)) is required, Applicants petitions for any required relief including extensions of

time and authorize the Commissioner to charge the cost of such petitions and/or other fees due in

connection with the filing of this document to Deposit Account No. 03-1952 referencing

204552033800.

Dated: December 19, 2005

Respectfully submitted.

Registration No.: 42,465

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Substitute for form 1449/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known				
Application Number 10/514,429				
Filing Date	July 12, 2005			
First Named Inventor	Robert DWILINSKI			
Art Unit	2879			
Examiner Name	Not Yet Assigned			
Attorney Docket Number	204552033800			

U.S. PATENT DOCUMENTS					
Examiner	Cita	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where
Initials*	Cite No. <sup>1</sup>	Number-Kind Code <sup>2</sup> (if known)	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
	1.	5,096,860-A	03-17-1992	NADKARNI	
	2.	5,589,153-A	12-31-1996	GARCES	
	3.	6,252,261-B1	06-26-2001	USUI	
	4.	6,468,882-B2	10-22-2002	МОТОКІ	
	5.	6,509,651-B1	01-21-2003	MATSUBARA	
	6.	6,720,586-B1	04-13-2004	KIDOGUCHI	
	7.	2002/0014631-A1	02-07-2002	IWATA	
	8.	2002/0031153-A1	03-14-2002	NIWA	
	9.	2002/0047113-A1	04-25-2002	OHNO	
	10.	2002/0063258-A1	05-30-2002	MOTOKI	
	11.	2002/0078881-A1	06-27-2002	СПОМО	
	12.	2004/0139912-A1	07-22-2004	TOMASZ DWILINSKI	·

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sub>6</sub>
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>		
	13.	Akasaki, I. et al. (1991). "Growth and Properties of Single Crystalline GaN Films by Hydride Vapor Phase Epitaxy," Crystal Properties and Preparation 32-34:154-157.			
	14.	Chu, T. L. et al. (1974). "Crystal Growth and Characterization of Gallium Nitride," <i>J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY</i> 121-1:159-162.			
	15.	Kaschner, A. et al. (1999). "Influence of Doping on the Lattice Dynamics of Gallium Nitride," MRS Internet J. Nitride Semicond. Res. 4S1, G3.57.			
	16.	Kim, S. T. et al. (1998). "Preparation and Properties of Free-standing HVPE Grown GaN Substrates," <i>Journal of Crystal Growth</i> 194:37-42.			
	17.	Kuroda, Naotaka et al. (1998). "Precise Control of Pn-junction Profiles for GaN-based LD structures Using GaN Substrates with Low Dislocation Densities," <i>Journal of Crystal Growth</i> 189/190:551-555.			
	18.	Motoki, Kensaku et al. (2001). "Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a Starting Substrate," J. Appl. Phys. 40:L140-L143.			

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Examiner	Date
Signature	Considered
1 10 10 0	

<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.